Icemos Technology Ltd Product Specification 1003.777005 Issue Date 16 June 2025 17:54:24

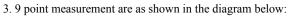
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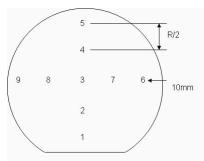
Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	100.00 +/- 0.20 mm	
	2.0	Primary Flat Orientation	{110} +/- 1 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none or SEMI Standard	Wafer Vendor
	5.0	Overall Thickness	450.00 +/- 50.00 μm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<10.00μm	Guaranteed by Process
	7.0	Bow	<40.00 μm	ADE to ASTM F534, 20%
	8.0	Warp	<40.00 μm	ADE to ASTM F637, 20%
	9.0	Edge Chips	0	Bright Light, 100%
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 1.0 degree	Wafer Vendor
	13.0	Handle Thickness	450.00 +/- 50.00 μm	ADE, 100%
	14.0	Handle Doping Type	Any	Wafer Vendor
	15.0	Handle Dopant	Any	Wafer Vendor
	16.0	Handle Resistivity	Any	Wafer Vendor
	17.0	Backside Finish	Polished with laser mark, chuck marks and handling per additional comments.	Guaranteed by process

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Part Number		Customer		
Category	Parameter	Specification	Measurement Method	
Shipping Details	Wafer per box :	Max 25		
	Packaging:	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging		
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness		
Explanatory Notes	1. Microscope inspec	ction performed using microscope scan as below. 5x objective.		
	2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall			

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overal Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.





Additional Information